



T-29-23

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistors in plastic TO-92 envelopes, primarily intended for use in driver and output stages of audio amplifiers.

The BC327, BC327A, BC328 are complementary to the BC337, BC337A and BC338 respectively.

QUICK REFERENCE DATA

		BC327	BC327A	BC328	
Collector-emitter voltage ( $V_{BE} = 0$ )	$-V_{CES}$ max.	50	60	30	V
Collector-emitter voltage (open base)	$-V_{CEO}$ max.	45	60	25	V
Collector current (peak value)	$-I_{CM}$ max.	1000			mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	$P_{tot}$ max.	800			mW
Junction temperature	$T_j$ max.	150			$^{\circ}\text{C}$
Transition frequency at $f = 35\text{ MHz}$ $-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$	$f_T$ typ.	100			MHz
D.C. current gain $-I_C = 100\text{ mA}; -V_{CE} = 1\text{ V}$	$h_{FE}$	100 to 600			

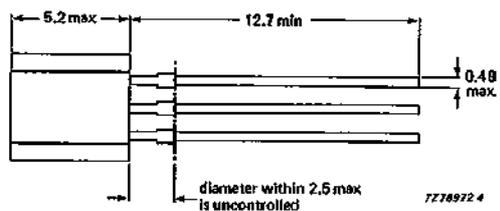
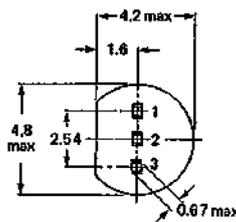
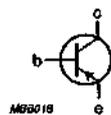
MECHANICAL DATA

Dimensions in mm

Fig. 1 TO-92.

Pinning

- 1 = emitter
- 2 = base
- 3 = collector



Capability approved to GECC NECC-C-002

**RATINGS**

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Limiting values in accordance with the Absolute Maximum System (IEC 134)

		BC327	BC327A	BC328	
Collector-emitter voltage ( $V_{BE} = 0$ )	$-V_{CES}$ max.	50	60	30	V
Collector-emitter voltage (open base) $-I_C = 10$ mA	$-V_{CEO}$ max.	45	60	25	V
Emitter-base voltage (open collector)	$-V_{EBO}$ max.	5	5	5	V
Collector current (d.c.)	$-I_C$ max.		500		mA
Collector current (peak value)	$-I_{CM}$ max.		1000		mA
Emitter current (peak value)	$I_{EM}$ max.		1000		mA
Base current (d.c.)	$-I_B$ max.		100		mA
Base current (peak value)	$-I_{BM}$ max.		200		mA
Total power dissipation at $T_{amb} = 25$ °C	$P_{tot}$ max.		625		mW
up to $T_{amb} = 25$ °C	$P_{tot}$ max.		800		mW*
Storage temperature	$T_{stg}$	-65 to +150			°C
Junction temperature	$T_j$ max.		150		°C
<b>THERMAL RESISTANCE</b>					
From junction to ambient in free air	$R_{th j-a}$ =		0,2		K/mW
From junction to ambient	$R_{th j-a}$ =		0,156		K/mW*

\* Transistor mounted on printed circuit board, max. lead length 4 mm, mounting pad for collector lead min. 10 mm x 10 mm.

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## CHARACTERISTICS

 $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

Collector cut-off current

 $I_E = 0; -V_{CB} = 20\text{ V}; T_j = 25\text{ }^\circ\text{C}$  $-I_{CBO} < 100\text{ nA}$  $I_E = 0; -V_{CB} = 20\text{ V}; T_j = 150\text{ }^\circ\text{C}$  $-I_{CBO} < 5\text{ }\mu\text{A}$ 

Emitter cut-off current

 $I_C = 0; -V_{EB} = 5\text{ V}$  $-I_{EBO} < 10\text{ }\mu\text{A}$ 

Base-emitter voltage\*

 $-I_C = 500\text{ mA}; -V_{CE} = 1\text{ V}$  $-V_{BE} < 1,2\text{ V}$ 

Saturation voltage

 $-I_C = 500\text{ mA}; -I_B = 50\text{ mA}$  $-V_{CEsat} < 700\text{ mV}$ 

D.C. current gain

 $-I_C = 500\text{ mA}; -V_{CE} = 1\text{ V}$  $h_{FE} > 40$  $-I_C = 100\text{ mA}; -V_{CE} = 1\text{ V};$  BC327; BC328 $h_{FE}$  100 to 600

BC327A

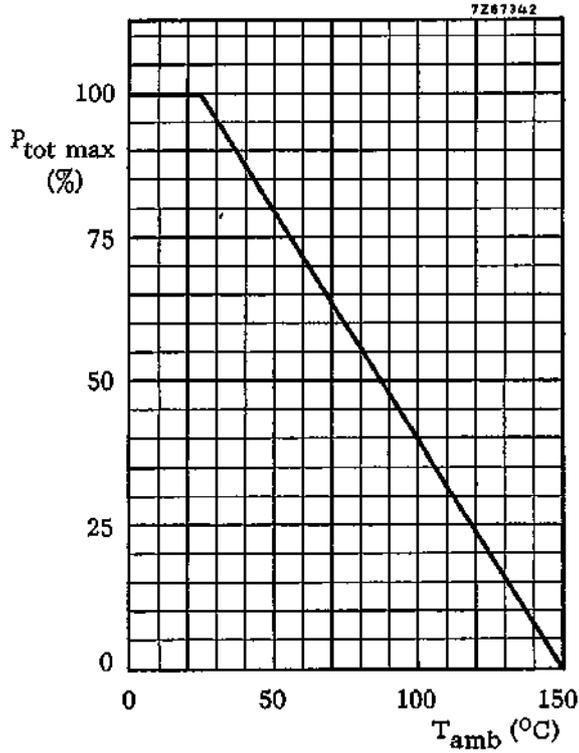
 $h_{FE}$  100 to 400BC327-16 }  
BC328-16 } $h_{FE}$  100 to 250BC327-25 }  
BC328-25 } $h_{FE}$  160 to 400BC327-40 }  
BC328-40 } $h_{FE}$  250 to 600Transition frequency at  $f = 35\text{ MHz}$  $-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$  $f_T$  typ. 100 MHzCollector capacitance at  $f = 1\text{ MHz}$  $I_E = I_e = 0; -V_{CB} = 10\text{ V}$  $C_c$  typ. 8 pF\*  $-V_{BE}$  decreases by about 2 mV/K with increasing temperature.

BC327  
BC327A  
BC328

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Fig. 2.

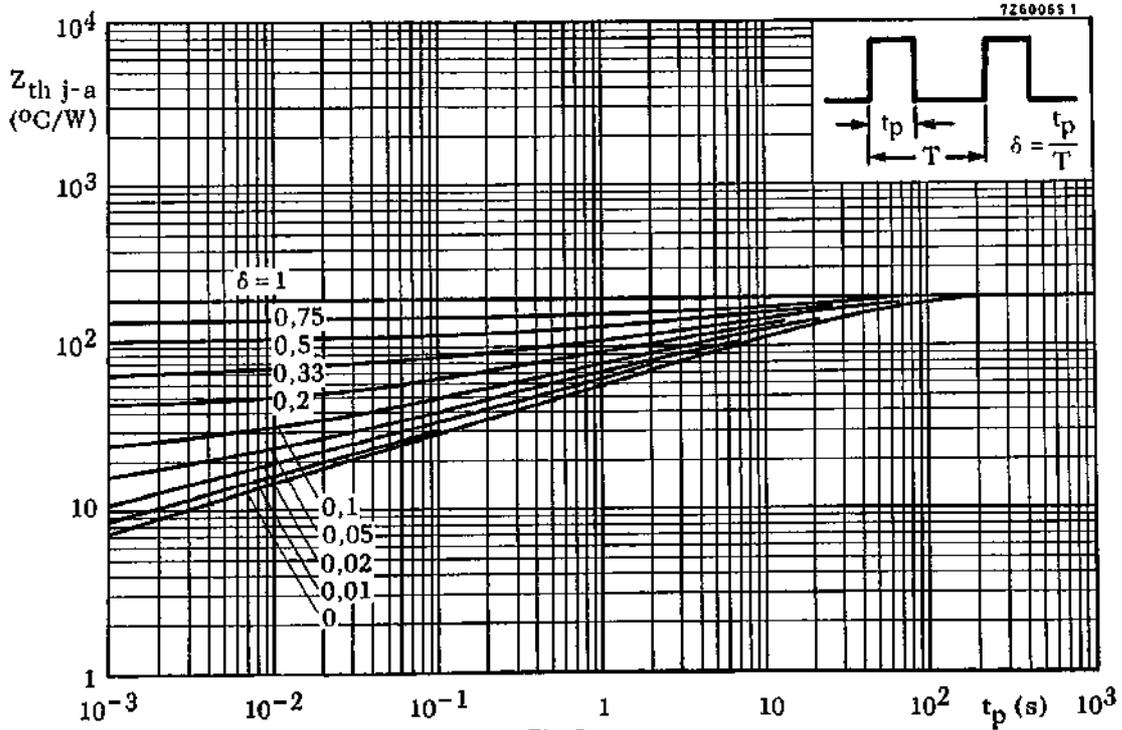


Fig. 3.

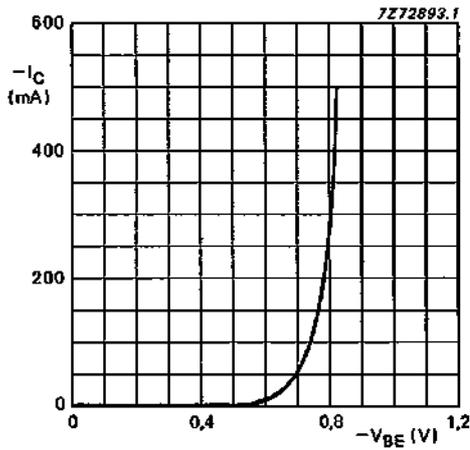


Fig. 4  $-V_{CE} = 1$  V;  $T_j = 25$  °C; typical values.

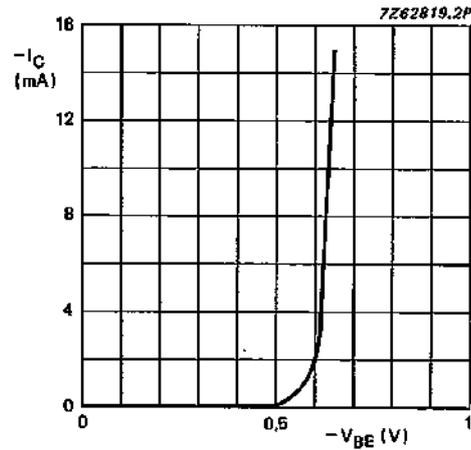


Fig. 5  $-V_{CE} = 5$  V;  $T_j = 25$  °C; typical values.

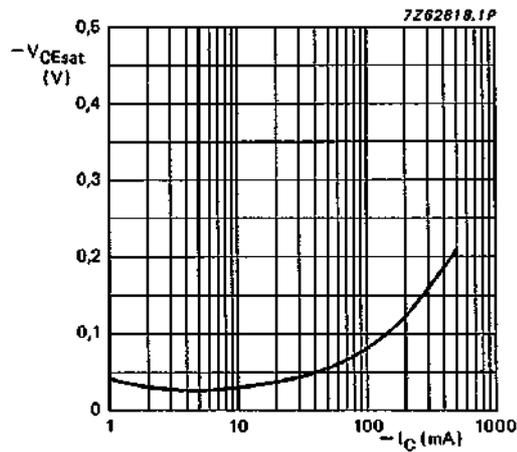


Fig. 6  $I_C/I_B = 10$ ;  $T_j = 25$  °C; typical values.

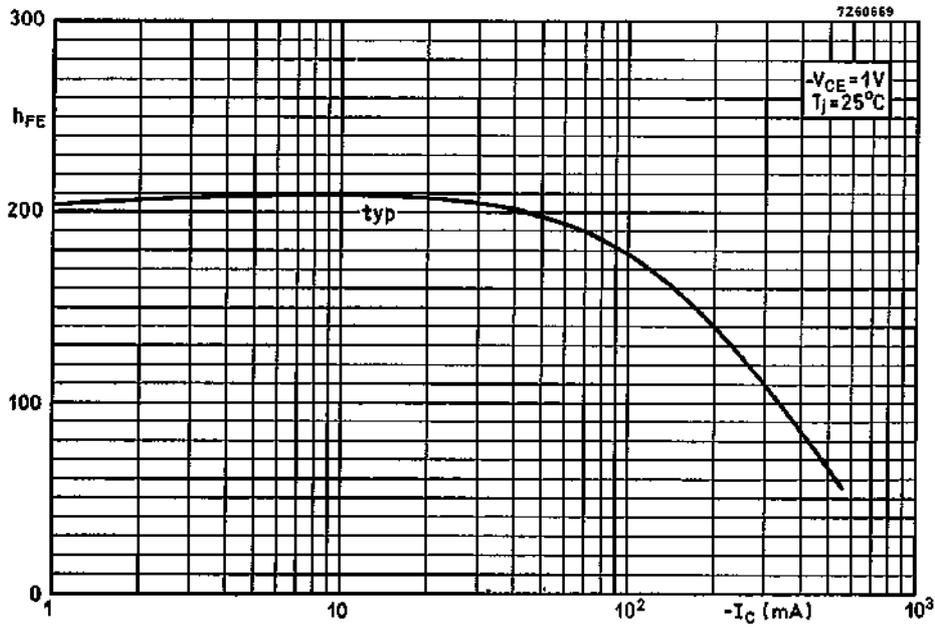


Fig. 7.

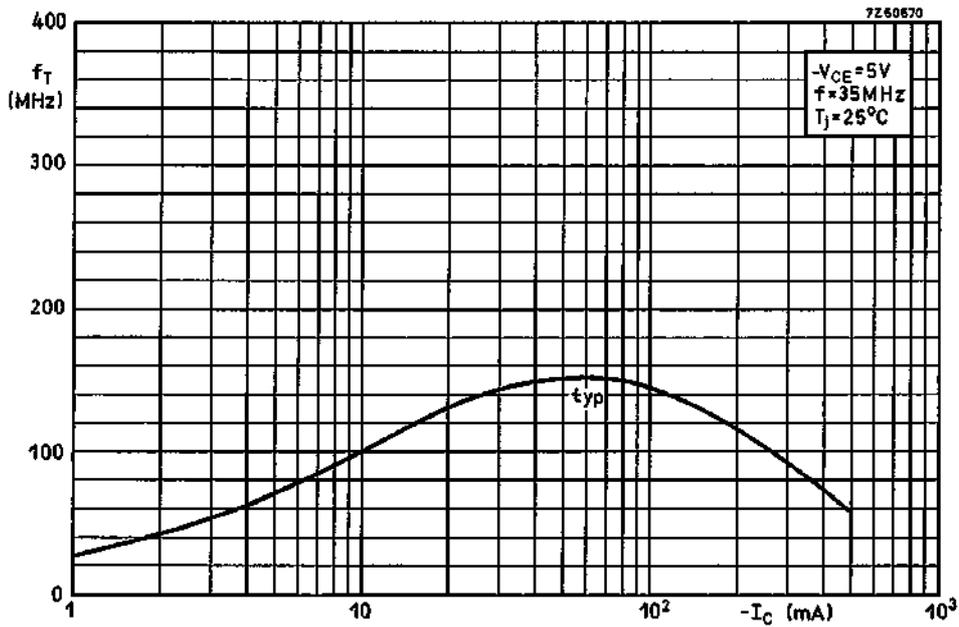


Fig. 8.